TDA8034HN

Low power smart card interface

Rev. 3.5 — 13 March 2020 Product data sheet

1. General description

The TDA8034HN is a cost-effective analog interface for asynchronous and synchronous smart cards operating at 5 V, 3 V or 1.8 V. Using few external components, the TDA8034HN provides all supply, protection and control functions between a smart card and the microcontroller.

2. Features and benefits

- Integrated circuit smart card interface in an HVQFN24 package
- 5 V, 3 V or 1.8 V smart card supply
- Very low power consumption in Deep Shutdown mode
- Three protected half-duplex bidirectional buffered I/O lines (C4, C7 and C8)
- V_{CC} regulation:
  - 5 V, 3 V or 1.8 V ± 5 % using two low ESR multilayer ceramic capacitors: one of 220 nF and one of 470 nF
  - current spikes of 40 nA/s (V_{CC} = 5 V and 3 V) or 15 nA/s (V_{CC} =1.8 V) up to 20 MHz, with controlled rise and fall times and filtered overload detection of approximately 120 mA
- Thermal and short-circuit protection for all card contacts
- Automatic activation and deactivation sequences triggered by a short-circuit, card take-off, overheating, falling V_{DD}, $V_{DD(INTF)}$ or V_{DDP}
- Enhanced card-side ElectroStatic Discharge (ESD) protection of > 8 kV
- External clock input up to 26 MHz connected to pin XTAL1
- Card clock generation up to 20 MHz using pins CLKDIV1 and CLKDIV2 with synchronous frequency changes of f_{xtal}, $\frac{1}{2}$ f_{xtal}, $\frac{1}{4}$ f_{xtal} or $\frac{1}{8}$ f_{xtal}
- Non-inverted control of pin RST using pin RSTIN
- Compatible with ISO 7816, NDS and EMVCo4.3 [1] payment systems
- Supply supervisor for killing spikes during power on and off:
  - using a fixed threshold
  - using an external resistor bridge with threshold adjustment
- Built-in debouncing on card presence contacts (typically 8 ms)
- Multiplexed status signal using pin OFFN

1. For C2 version

3. Applications

- Pay TV
- Electronic payment
- Identification
- Bank card readers

4. Quick reference data

Table 1. Quick reference data

V_{DDP} = 5 V; V_{DD} = 3.3 V; $V_{DD(INTF)}$ = 3.3 V; f_{xtal} = 10 MHz; GND = 0 V; T_{amb} = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Supply						
V_{DDP}	power supply voltage	pin V_{DDP}; regulator input				
		V_{CC} = 5 V	4.85	5	5.5	V
		V_{CC} = 3 V and 1.8 V	3	3.3	5.5	V
V_{DD}	supply voltage	pin V_{DD}	2.7	3.3	3.6	V
$V_{DD(INTF)}$	interface supply voltage	pin $V_{DD(INTF)}$	1.6	3.3	V_{DD} + 0.3	V
I_{DD}	supply current	shutdown mode	-	-	35	µA
		deep shutdown mode	-	-	12	µA
		active mode	-	-	2	mA
I_{DDP}	power supply current	shutdown mode; f_{xtal} stopped	-	-	5	µA
		active mode; f_{CLK} = ½ f_{xtal}; no load	-	-	1.5	mA
$I_{DD(INTF)}$	interface supply current	shutdown mode	-	-	6	µA
		active mode	-	-	2	mA
Card supply voltage: pin V_{CC}[1]						
V_{CC}	supply voltage	active mode; I_{CC} < 65 mA DC				
		5 V card	4.75	5.0	5.25	V
		3 V card	2.85	3.05	3.15	V
		1.8 V card	1.71	1.83	1.89	V
		active mode; current pulses of 40 nA/s at I_{CC} < 200 mA; t < 400 ns				
		5 V card	4.65	5.0	5.25	V
		3 V card	2.76	-	3.20	V
		active mode; current pulses of 15 nA/s at I_{CC} < 200 mA, t < 400 ns; 1.8 V card	1.66	-	1.94	V
$V_{ripple(p-p)}$	peak-to-peak ripple voltage	from 20 kHz to 200 MHz	-	-	350	mV
I_{CC}	supply current	V_{CC} = 0 V to 5 V, 3 V or 1.8 V	-	-	65	mA
General						
t_{deact}	deactivation time	see Figure 8 on page 12	35	90	250	µs
P_{tot}	total power dissipation	T_{amb} = −25 °C to +85 °C	-	-	0.25	W
T_{amb}	ambient temperature		−25	-	+85	°C

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[1] To meet these specifications, V_{CC} should be decoupled to pin GND using two ceramic multilayer capacitors of low ESR with values of either 100 nF or one 220 nF and one 470 nF.

5. Ordering information

The TDA8034HN is available in 2 versions. Both have the same functionality. C2 version is compliant with EMVCo 4.3

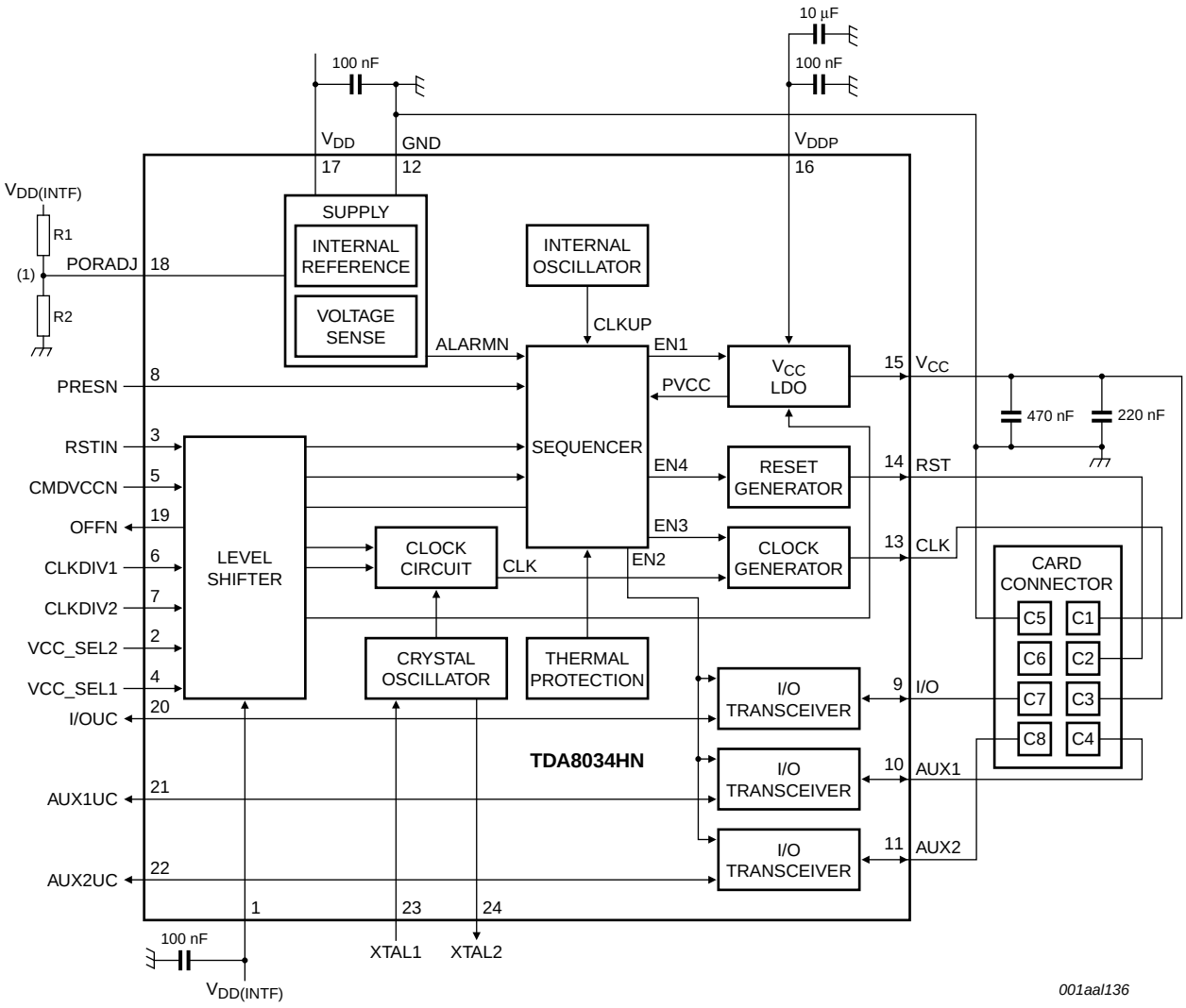
Table 2. Ordering information

Type number	Package		
	Name	Description	Version
TDA8034HN/C1	HVQFN24	plastic thermal enhanced very thin quad flat package; no leads; 24 terminals; body 4 × 4 × 0.85 mm	SOT616-1
TDA8034HN/C2	HVQFN24	plastic thermal enhanced very thin quad flat package; no leads; 24 terminals; body 4 × 4 × 0.85 mm	SOT616-1

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6. Block diagram



ALARMN, CLKUP, EN1, PVCC, EN4, EN3, EN2 and CLK are internal signals.

(1) Optional external resistor bridge, if not required connect pin PORADJ to $V_{DD(INTF)}$

Fig 1. Block diagram

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7. Pinning information

7.1 Pinning

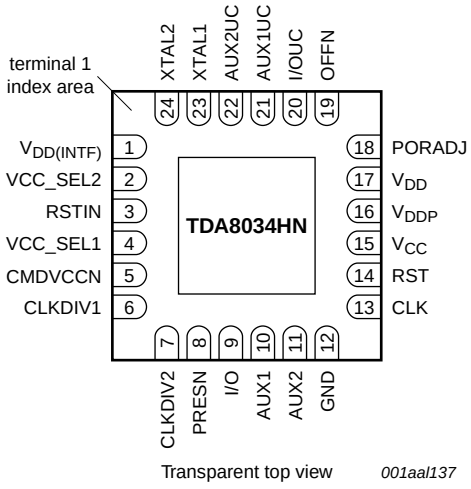


Fig 2. Pin configuration

7.2 Pin description

Table 3. Pin description

Symbol	Pin	Supply	Type[1]	Description
$V_{DD(INTF)}$	1	$V_{DD(INTF)}$	P	interface supply voltage
VCC_SEL2	2	$V_{DD(INTF)}$	I	5 V or 3 V V_{CC} voltage selection control signal:
				active LOW: V_{CC} = 3 V when pin VCC_SEL1 is HIGH
				active HIGH: V_{CC} = 5 V
RSTIN	3	$V_{DD(INTF)}$	I	microcontroller card reset input; active HIGH
VCC_SEL1	4	$V_{DD(INTF)}$	I	1.8 V V_{CC} voltage selection control signal:
				active LOW: V_{CC} = 1.8 V
				active HIGH: disables 1.8 V selection
CMDVCCN	5	$V_{DD(INTF)}$	I	microcontroller start activation sequence input; active LOW
CLKDIV1	6	$V_{DD(INTF)}$	I	sets the clock frequency on pin CLK in association with pin CLKDIV2; see Table 4
CLKDIV2	7	$V_{DD(INTF)}$	I	sets the clock frequency on pin CLK in association with pin CLKDIV1; see Table 4
PRESN	8	$V_{DD(INTF)}$	I	card presence contact input; active LOW[2]
I/O	9	V_{CC}	I/O	card input/output data line (C7)[3]
AUX1	10	V_{CC}	I/O	auxiliary card input/output data line (C4)[3]
AUX2	11	V_{CC}	I/O	auxiliary card input/output data line (C8)[3]
GND	12	-	G	ground
CLK	13	V_{CC}	O	card clock (C3)
RST	14	V_{CC}	O	card reset (C2)
V_{CC}	15	V_{CC}	P	card supply (C1); decouple to pin GND using one 470 nF capacitor close to pin V_{CC} and one 220 nF capacitor close to card socket contact C1 with an ESR < 100 mΩ

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Table 3. Pin description *...continued*

Symbol	Pin	Supply	Type[1]	Description
V_{DDP}	16	V_{DDP}	P	low-dropout regulator input supply voltage
V_{DD}	17	V_{DD}	P	digital supply voltage
PORADJ	18	$V_{DD(INTF)}$	I	power-on reset threshold adjustment input using an optional external resistor bridge
OFFN	19	$V_{DD(INTF)}$	O	NMOS interrupt to microcontroller[4]; active LOW; see Section 8.10 on page 12
I/OUC	20	$V_{DD(INTF)}$	I/O	microcontroller input/output data line[5]
AUX1UC	21	$V_{DD(INTF)}$	I/O	auxiliary microcontroller input/output data line[5]
AUX2UC	22	$V_{DD(INTF)}$	I/O	auxiliary microcontroller input/output data line[5]
XTAL1	23	V_{DD}	I	crystal connection input
XTAL2	24	V_{DD}	O	crystal connection output

[1] I = input, O = output, I/O = input/output, G = ground and P = power supply.

[2] If pin PRESN is LOW, the card is considered to be present. During card insertion, debouncing can occur on these signals. To counter this, the TDA8034HN has a built-in debouncing timer (typically 8 ms).

[3] Uses an internal 11 kΩ pull-up resistor connected to pin V_{CC}.

[4] Uses an internal 20 kΩ pull-up resistor connected to pin $V_{DD(INTF)}$.

[5] Uses an internal 10kW pull-up resistor connected to pin $V_{DD(INTF)}$

8. Functional description

Remark: Throughout this document the ISO 7816 terminology conventions have been adhered to and it is assumed that the reader is familiar with these.

8.1 Power supplies

The power supply voltage ranges are as follows:

- V_{DDP}: 4.85 V to 5.5 V when VCC_SEL2 is HIGH (V_{CC} = 5 V)
- V_{DDP}: 3 V to 5.5 V when VCC_SEL2 is LOW (V_{CC} = 3 V) or when VCC_SEL1 is LOW (V_{CC} = 1.8 V)
- V_{DD}: 2.7 V to 3.6 V

All interface signals to the system controller are referenced to $V_{DD(INTF)}$. All card contacts remain inactive during power up or power down. After powering up the device, pin OFFN remains LOW until pin CMDVCCN is set HIGH and pin PRESN is LOW. During power down, pin OFFN goes LOW when V_{DDP} falls below the falling threshold voltage (V_{th}).

The internal oscillator frequency ($f_{osc(int)}$) is only used during the activation sequences. When the card is not activated (pin CMDVCCN is HIGH), the internal oscillator is in low frequency mode to reduce power consumption.

This device has a Low Drop-Off (LDO) voltage regulator connected to pin V_{CC}, and is used instead of a DC-to-DC converter. It ensures a minimum V_{CC} of 4.75 V and that the power supply voltage on pin V_{DDP} does not fall below 4.85 V when pin VCC_SEL2 is HIGH, for a maximum load current of 65 mA.

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In case the 3 power supply VDD, VDDP, VDD(INTF) are connected together (VDD =VDDP= VDD(INTF)) and if the power up slope is faster than 1ms (10%-90% slope<1ms), a deep shutdown sequence must be performed once the supplies have reached steady state; this means CMDVCCN is set high while VCC_SEL1 and VCC_SEL2 forced to low level (see Section 8.6 “Deep shutdown mode”).

8.2 Voltage supervisor

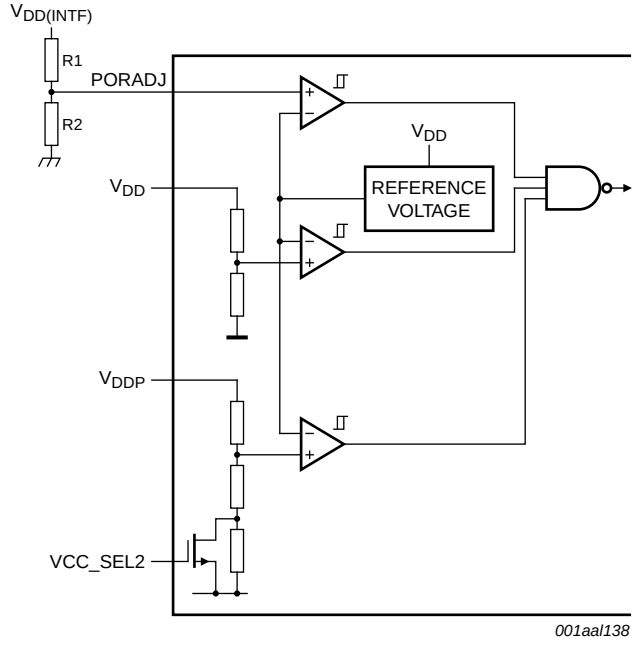


Fig 3. Voltage supervisor circuit

The voltage supervisor monitors the voltage of the V_{DDP}, V_{DD} and $V_{DD(INTF)}$ supplies providing both Power-On Reset (POR) and supply drop-out detection during a card session. The supervisor threshold voltages for V_{DDP} and V_{DD} are set internally, and for $V_{DD(INTF)}$ externally by pin PORADJ. As long as V_{DD} is less than $V_{th} + V_{hys}$, the IC remains inactive irrespective of the command line levels. After V_{DD} has reached a level higher than $V_{th} + V_{hys}$, the IC remains inactive for the duration of t_w. The output of the supervisor is sent to a digital controller in order to reset the TDA8034HN. This defined reset pulse of approximately 8 ms, i.e. ($t_w = 1024 \times {}^{1}/_{f_{osc(int)low}}$), is used internally to maintain the IC in the Shutdown mode during the supply voltage power on; see Figure 4. A deactivation sequence is performed when either V_{DD}, V_{DDP} or $V_{DD(INTF)}$ falls below V_{th}.

Remark: $f_{osc(int)low}$ is the low frequency (or inactive) mode of the defined $f_{osc(int)}$ parameter.

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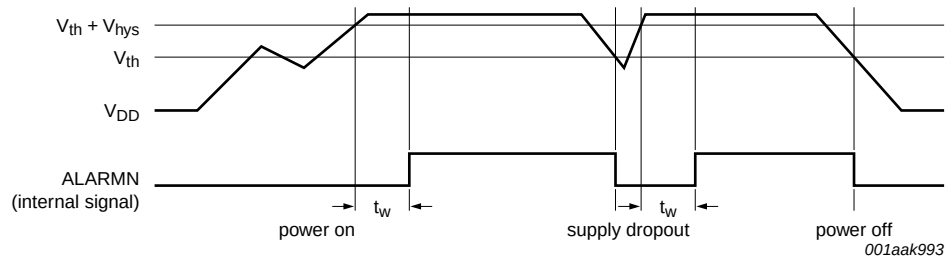
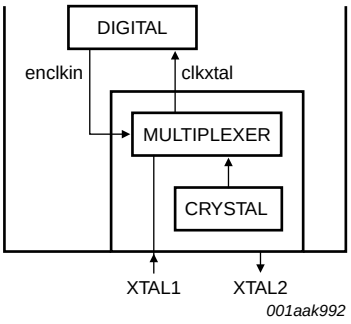


Fig 4. Voltage supervisor waveforms

8.3 Clock circuits

The clock signal from pin CLK to the card is either supplied by an external clock signal connected to pin XTAL1 or generated using a crystal connected between pins XTAL1 and XTAL2. The TDA8034HN automatically detects if an external clock is connected to XTAL1, eliminating the need for a separate pin to select the clock source.

Automatic clock source detection is performed on each activation command (falling edge of the signal on pin CMDVCCN). The presence of an external clock on pin XTAL1 is checked during a time window defined by the internal oscillator. If a clock is detected, the internal crystal oscillator is stopped. If a clock is not detected, the internal crystal oscillator is started. When an external clock is used, it is mandatory that the clock is applied to pin XTAL1 before the falling edge of the signal on pin CMDVCCN.



enclkin and clkxtal are internal signal names.

Fig 5. Basic layout for using an external clock

The clock frequency is selected using pins CLKDIV1 and CLKDIV1 to be either f_{xtal}, $\frac{1}{2} f_{xtal}$ or $\frac{1}{4} f_{xtal}$ or $\frac{1}{8} f_{xtal}$ as shown in Table 4.

Remark: The levels on both pins must not be allowed to change simultaneously but should be separated by a minimum of 10 ns.

The frequency change is synchronous and as such during transition, no pulse is shorter than 45 % of the smallest period. In addition, only the first and last clock pulse around the change has the correct width. When dynamically changing the frequency, the modification is only effective after 10 clock periods on pin XTAL1.

The duty cycle of f_{xtal} on pin CLK should be between 45 % and 55 %. If an external clock is connected to pin XTAL1, its duty cycle must be between 48 % and 52 %.

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When the frequency of the clock signal on pin CLK is either f_{xtal}, $\frac{1}{2} f_{xtal}$, $\frac{1}{4} f_{xtal}$ or $\frac{1}{8} f_{xtal}$, the frequency dividers guarantee a duty cycle between 45 % and 55 %.

Table 4. Clock configuration

Pin CLKDIV1 level	Pin CLKDIV2 level	Pin CLK frequency
LOW	LOW	$\frac{1}{8} f_{xtal}$
LOW	HIGH	$\frac{1}{4} f_{xtal}$
HIGH	HIGH	$\frac{1}{2} f_{xtal}$
HIGH	LOW	f_{xtal}

8.4 Input and output circuits

When pins I/O and I/OUC are pulled HIGH using an 11 kΩ resistor between pins I/O and V_{CC} and/or between pins I/OUC and $V_{DD(INTF)}$, both lines enter the idle state. Pin I/O is referenced to V_{CC} and pin I/OUC to $V_{DD(INTF)}$, thus allowing operation at $V_{CC} \neq V_{DD(INTF)}$.

The first side on which a falling edge occurs becomes the master. An anti-latch circuit disables falling edge detection on the other line, making it the slave. After a time delay t_d, the logic 0 present on the master-side is sent to the slave-side. When the master-side returns logic 1, the slave-side sends logic 1 during time delay ($t_{w(pu)}$). After this sequence, both master and slave sides return to their idle states.

The active pull-up feature ensures fast LOW-to-HIGH transitions making the TDA8034HN capable of delivering more than 1 mA, up to an output voltage of $0.9V_{CC}$, at a load of 80 pF. At the end of the active pull-up pulse, the output voltage is dependent on the internal pull-up resistor value and load current. The current sent to and received from the card's I/O lines is limited to 15 mA at a maximum frequency of 1 MHz.

8.5 Shutdown mode

After a power-on reset, if pin CMDVCCN is HIGH, the circuit enters the Shutdown mode, ensuring only the minimum number of circuits are active while the TDA8034HN waits for the microcontroller to start a session.

- all card contacts are inactive. The impedance between the contacts and GND is approximately 200 Ω.
- pins I/OUC, AUX1UC and AUX2UC are high-impedance using the 11 kΩ pull-up resistor connected to $V_{DD(INTF)}$
- the voltage generators are stopped
- the voltage supervisor is active
- the internal oscillator runs at its lowest frequency ($f_{osc(int)low}$)

8.6 Deep shutdown mode

When the smart card reader is inactive, the TDA8034HN will enter Deep shutdown mode if pin CMDVCCN is forced HIGH and pins VCC_SEL1 and VCC_SEL2 are LOW. In Deep shutdown mode, all circuits are disabled and pin OFFN follows the status of pin PRESN. Changing the status of either pin CMDVCCN, VCC_SEL1 or VCC_SEL2 exits Deep shutdown mode; see Figure 6.

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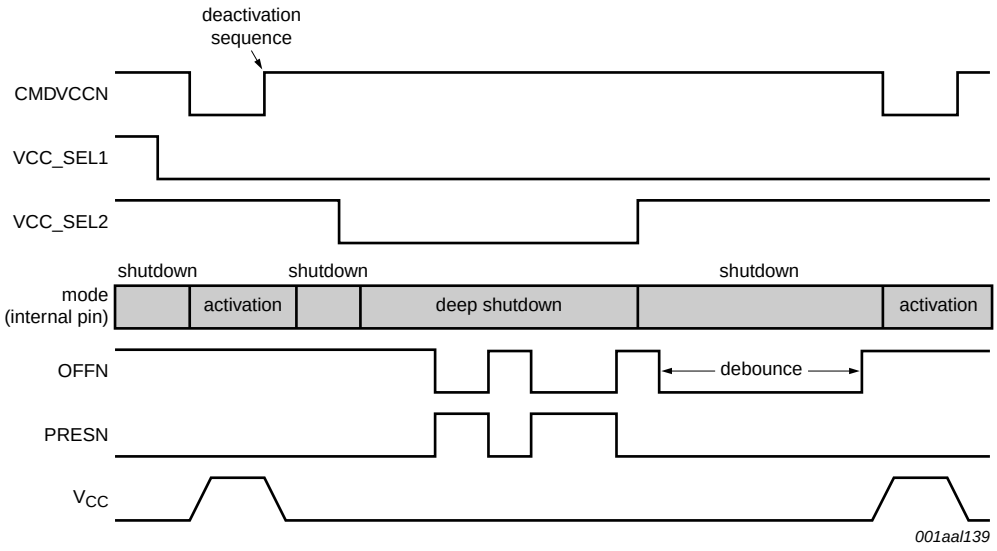


Fig 6. Shutdown and Deep shutdown mode activation/deactivation

8.7 Activation sequence

The following device activation sequence is applied when using an external clock; see Figure 7:

1. Pin CMDVCCN is pulled LOW (t0).
2. The internal oscillator is triggered (t0).
3. The internal oscillator changes to high frequency (t1).
4. V_{CC} rises from either 0 V to 3 V or 0 V to 5 V on a controlled slope (t2).
5. Pins I/OUC, AUX1UC and AUX2UC are driven HIGH (t3).
6. The clock on pin CLK is applied to the C3 contact (t4).
7. Pin RST is enabled (t5).

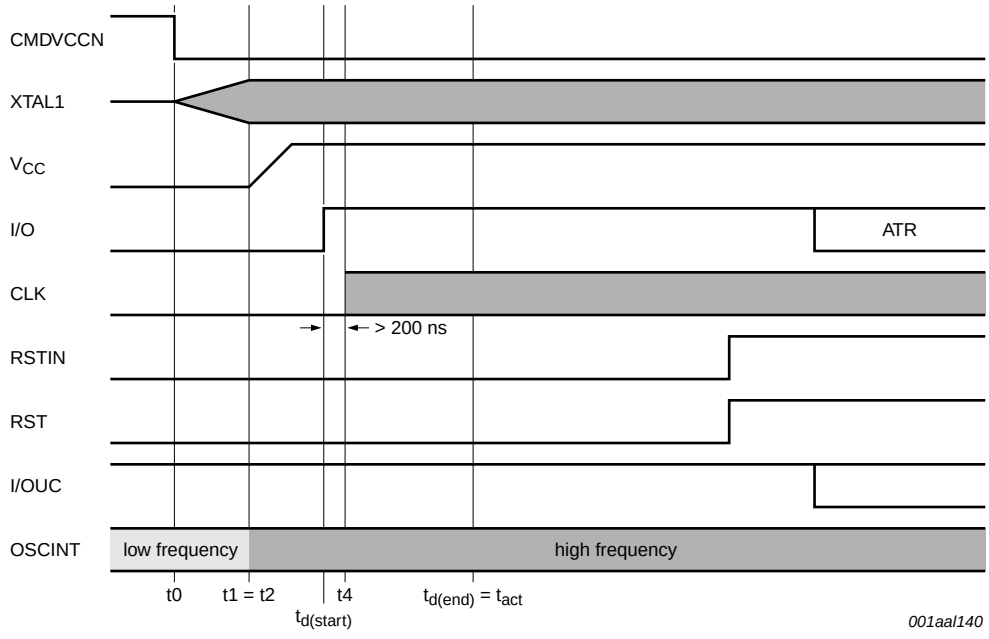
Calculation of the time delays is as follows:

- t1 = t0 + 384 × $1/f_{osc(int)low}$
- t2 = t1
- t3 = t1 + 17T / 2
- t4 = driven by host controller; > t3 and < t5
- t5 = t1 + 23T / 2

Remark: The value of period T is 64 times the period interval of the internal oscillator at high frequency ($1/f_{osc(int)high}$); t3 is called $t_{d(start)}$ and t5 is called $t_{d(end)}$.

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OSCINT = internal oscillator.

Fig 7. Activation sequence at t3

8.8 Deactivation sequence

When a session ends, the microcontroller sets pin CMDVCCN HIGH. The TDA8034HN then executes an automatic deactivation sequence by counting the sequencer back to the inactive state (see Figure 8) as follows:

1. Pin RST is pulled LOW (t11).
2. The clock is stopped, pin CLK is LOW (t12).
3. Pins I/OUC, AUX1UC and AUX2UC are pulled LOW (t13).
4. V_{CC} falls to 0 V (t14). The deactivation sequence is completed when V_{CC} reaches its inactive state.
5. V_{CC} < 0.4 V (t_{deac})
6. All card contacts become low-impedance to GND. However, pins I/OUC, AUX1UC and AUX2UC remain pulled up to V_{DD} using the 11 kΩ resistor.
7. The internal oscillator returns to its low frequency mode.

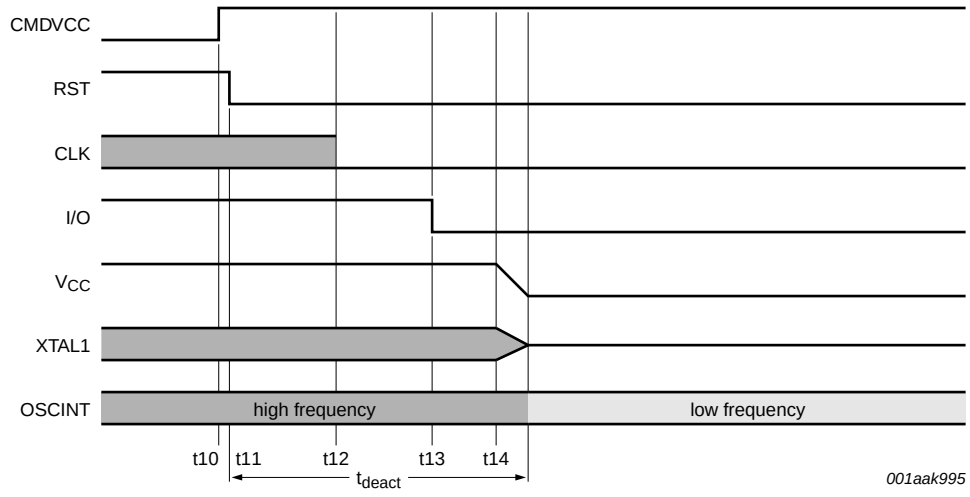
Calculation of the time delays is as follows:

- t11 = t10 + 3T / 64
- t12 = t11 + T / 2
- t13 = t11 + T
- t14 = t11 + 3T / 2
- t_{deac} = t11 + 3T / 2 + V_{CC} fall time

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Remark: The value of period T is 64 times the period interval of the internal oscillator (i.e. ± 25 μs).



OSCINT = internal oscillator.

Fig 8. Deactivation sequence

8.9 V_{CC} regulator

The V_{CC} buffer is able to continuously deliver up to 65 mA at V_{CC} = 5 V, 3 V, or 1.8 V.

The V_{CC} buffer has an internal overload protection with a threshold value of approximately 120 mA. This detection is internally filtered, enabling spurious current pulses up to 200 mA with a duration of a few milliseconds to be drawn by the card without causing deactivation. However, the average current value must stay below maximum; see Table 8.

8.10 Fault detection

The following conditions are monitored by the fault detection circuit:

- Short-circuit or high current on pin V_{CC}
- Card removal during transaction
- V_{DDP} falling
- V_{DD} falling
- $V_{DD(INTF)}$ falling
- Overheating

Fault detection monitors two different situations:

- Outside card sessions, pin CMDVCCN is HIGH: pin OFFN is LOW if the card is not in the reader and HIGH if the card is in the reader. Any voltage drop on V_{DD} is detected by the voltage supervisor. This generates an internal power-on reset pulse but does not act upon the pin OFFN signal. The card is not powered-up and short-circuits or overheating are not detected.

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- In card sessions, pin CMDVCCN is LOW: when pin OFFN goes LOW, the fault detection circuit triggers the automatic emergency deactivation sequence (see Figure 9). When the microcontroller resets pin CMDVCCN to HIGH, after the deactivation sequence, pin OFFN is rechecked. If the card is still present, pin OFFN returns to HIGH. This check identifies the fault as either a hardware problem or a card removal incident.

On card insertion or removal, bouncing can occur in the PRESN signal. This depends on the type of card presence switch in the connector (normally open or normally closed) and the mechanical characteristics of the switch. To correct for this, a debouncing feature is integrated in to the TDA8034HN. This feature operates at a typical duration of 8 ms (t_{deb} = 640 × ($1/f_{osc(int)low}$). Figure 10 on page 14 shows the operation of the debouncing feature.

On card insertion, pin OFFN goes HIGH after the debounce time has elapsed. When the card is extracted, the automatic card deactivation sequence is performed on the first HIGH/LOW transition on pin PRESN. After this, pin OFFN goes LOW.

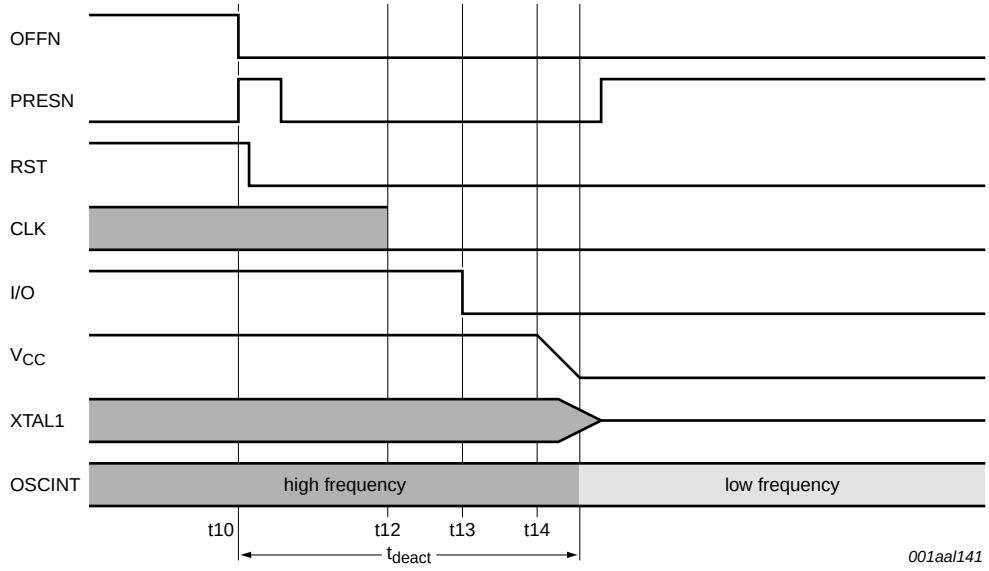
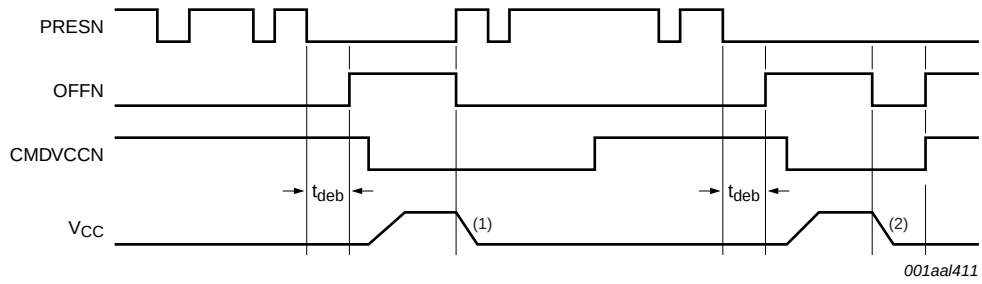


Fig 9. Emergency deactivation sequence after card removal

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(1) Deactivation caused by card withdrawal.

(2) Deactivation caused by short-circuit.

Fig 10. Operation of debounce feature with pins OFFN, CMDVCCN, PRESN and V_{CC}

9. Limiting values

Remark: All card contacts are protected against any short-circuit to any other card contact. Stress beyond the levels indicated in Table 5 can cause permanent damage to the device. This is a short-term stress rating only and under no circumstances implies functional operation under long-term stress conditions.

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DDP}	power supply voltage	pin V_{DDP}	−0.3	+6	V
V_{DD}	supply voltage	pin V_{DD}	−0.3	+4.6	V
$V_{DD(INTF)}$	interface supply voltage	pin $V_{DD(INTF)}$	−0.3	+4.6	V
V_I	input voltage	pins CMDVCCN, CLKDIV1, CLKDIV2, VCC_SEL1, VCC_SEL2, RSTIN, OFFN, PORADJ, XTAL1, XTAL2, I/OUC, AUX1UC, AUX1UC	−0.3	+4.6	V
		card contact pins PRESN, I/O, RST, AUX1, AUX2 and CLK	−0.3	+6	V
T_{stg}	storage temperature		−55	+150	°C
P_{tot}	total power dissipation	T_{amb} = −25 °C to +85 °C	-	0.25	W
T_j	junction temperature		-	+125	°C
T_{amb}	ambient temperature		−25	+85	°C
V_{ESD}	electrostatic discharge voltage	Human Body Model (HBM) on card pins I/O, RST, V_{CC}, AUX1, AUX2, CLK; within typical application	−8	+8	kV
		Human Body Model (HBM); all other pins[1]	−2	+2	kV
		Machine Model (MM); all pins	−200	+200	V
		Field Charged Device Model (FCDM); all pins	−500	+500	V

[1] The PRESN pin supports ESD HBM discharge up to 7kV

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10. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Package name	Parameter	Conditions		Typ	Unit
$R_{th(j-a)}$	HVQFN24	thermal resistance from junction to ambient	in free air		53	K/W

11. Characteristics

Table 7. Characteristics of IC supply voltage

V_{DDP} = 5 V; V_{DD} = 3.3 V; $V_{DD(INTF)}$ = 3.3 V; f_{xtal} = 10 MHz; GND = 0 V; T_{amb} = 25 °C; for C1 and C2 versions; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Supply						
V_{DDP}	power supply voltage	pin V_{DDP}				
		V_{CC} = 5 V	4.85	5	5.5	V
		V_{CC} = 3 V or 1.8 V	3	3.3	5.5	V
V_{DD}	supply voltage	pin V_{DD}	2.7	3.3	3.6	V
$V_{DD(INTF)}$	interface supply voltage	pin $V_{DD(INTF)}$	1.6	3.3	V_{DD} + 0.3	V
I_{DD}	supply current	shutdown mode	-	-	35	µA
		deep shutdown mode	-	-	12	µA
		active mode	-	-	2	mA
I_{DDP}	power supply current	shutdown mode				
		f_{xtal} stopped	-	-	5	µA
		active mode				
		f_{CLK} = ½ f_{xtal}; no load	-	-	1.5	mA
		f_{CLK} = ½ f_{xtal}; I_{CC} = 65 mA	-	-	70	mA
$I_{DD(INTF)}$	interface supply current	shutdown mode	-	-	6	µA
		active mode	-	-	2	mA
V_{th}	threshold voltage	no external resistors on pin PORADJ				
		pin V_{DD} falling	2.30	2.40	2.50	V
		pin V_{DDP} falling; V_{CC} = 5 V	3.00	4.10	4.40	V
		external resistors on pin PORADJ	1.20	1.24	1.29	V
V_{hys}	hysteresis voltage	no external resistors on pin PORADJ				
		pin V_{DD}	50	100	150	mV
		pin V_{DDP}; V_{CC} = 5 V	100	200	350	mV
t_w	pulse width		5.1	8	10.2	ms
I_L	leakage current	pin PORADJ < 0.5 V	−0.1	+4	+10	µA
		pin PORADJ > 1 V	−1	-	+1	µA
Card supply voltage: pin V_{CC}[1]						
C_{dec}	decoupling capacitance	connected to V_{CC} [2]	550	-	830	nF

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Table 7. Characteristics of IC supply voltage *...continued*

V_{DDP} = 5 V; V_{DD} = 3.3 V; $V_{DD(INTF)}$ = 3.3 V; f_{xtal} = 10 MHz; GND = 0 V; T_{amb} = 25 °C; for C1 and C2 versions; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_o	output voltage	Shutdown mode				
		no load	−0.1	-	+0.1	V
		I_o = 1 mA	−0.1	-	+0.3	V
I_o	output current	Shutdown mode; pin V_{CC} connected to ground	-	-	−1	mA
V_{CC}	supply voltage	5 V card; Active mode : I_{CC} < 65 mA DC	4.75	5.0	5.25	V
		3 V card; Active mode : I_{CC} < 65 mA DC	2.85	3.05	3.15	V
		1.8 V card; Active mode : I_{CC} < 35 mA DC	1.71	1.83	1.89	V
		5 V card; active mode; current pulses of 40 nA/s at I_{CC} < 200 mA; t < 400 ns	4.65	5.0	5.25	V
		3 V card; active mode; current pulses of 40 nA/s at I_{CC} < 200 mA; t < 400 ns	2.76	-	3.20	V
		1.8 V card; active mode; current pulses of 15 nA/s at I_{CC} < 200 mA, t < 400 ns;	1.66	-	1.94	V
$V_{ripple(p-p)}$	peak-to-peak ripple voltage	20 kHz to 200 MHz	-	-	350	mV
I_{CC}	supply current	V_{CC} = 0 V to 5 V, 3 V or 1.8 V	-	-	65	mA
		V_{CC} shorted to ground	90	120	150	mA
SR	slew rate	5 V card	0.055	0.18	0.3	V/µs
		3 V card	0.040	0.18	0.3	V/µs
		1.8 V card	0.025	0.18	0.3	V/µs
Crystal oscillator: pins XTAL1 and XTAL2						
C_{ext}	external capacitance	pins XTAL1 and XTAL2 (depending on the crystal or resonator specification)	-	-	15	pF
f_{xtal}	crystal frequency	card clock reference; crystal oscillator	2	-	26	MHz
f_{ext}	external frequency	external clock on pin XTAL1	0	-	26	MHz
V_{IL}	LOW-level input voltage	crystal oscillator	−0.3	-	$+0.3V_{DD}$	V
		external clock	−0.3	-	$+0.3V_{DD(INTF)}$	V
V_{IH}	HIGH-level input voltage	crystal oscillator	$0.7V_{DD}$	-	V_{DD} + 0.3	V
		external clock	$0.7V_{DD(INTF)}$	-	$V_{DD(INTF)}$ + 0.3	V
Data lines: pins I/O, I/OUC, AUX1, AUX2, AUXIUC and AUX2UC						
t_d	delay time	falling edge on pins I/O and I/OUC or vise versa	-	-	200	ns

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Table 7. Characteristics of IC supply voltage *...continued*

V_{DDP} = 5 V; V_{DD} = 3.3 V; $V_{DD(INTF)}$ = 3.3 V; f_{xtal} = 10 MHz; GND = 0 V; T_{amb} = 25 °C; for C1 and C2 versions; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{w(pu)}$	pull-up pulse width		200	-	400	ns
f_{io}	input/output frequency	on data lines	-	-	1	MHz
C_i	input capacitance	on data lines	-	-	10	pF
Data lines to the card: pins I/O, AUX1and AUX2[3]						
V_o	output voltage	Shutdown mode				
		no load	0	-	0.1	V
		I_o = 1 mA	0	-	0.3	V
I_o	output current	Shutdown mode; pin I/O grounded	-	-	−1	mA
V_{OL}	LOW-level output voltage	I_{OL} = 1 mA- C1 version	0	-	0.3	V
		I_{OL} = 1 mA- C2 version	0	-	0.15 V_{CC}	V
		$I_{OL} \geq$ 15 mA	V_{CC} − 0.4	-	V_{CC}	V
V_{OH}	HIGH-level output voltage	no DC load	0.9V_{CC}	-	V_{CC} + 0.1	V
		$I_{OH} \geq$ −15 mA	0	-	0.4	V
		C1 version				
		I_{OH} < −40 µA; 5 V or 3 V	0.75V_{CC}	-	V_{CC} + 0.1	V
		I_{OH} < −20 µA; 1.8 V	0.75V_{CC}	-	V_{CC} + 0.1	V
		C2 version				
		I_{OH} < −40 µA; 5 V or 3 V	0.8 V_{CC}	-	V_{CC} + 0.1	V
		I_{OH} < −20 µA; 1.8 V	1.28	-	V_{CC} + 0.1	V
V_{IL}	LOW-level input voltage	C1 version	−0.3	-	+0.8	V
		C2 version	−0.3	-	0.2 V_{CC}	V
V_{IH}	HIGH-level input voltage	C1 version				
		V_{CC} = 5 V	0.6V_{CC}	-	V_{CC} + 0.3	V
		V_{CC} = 3 V or 1.8 V	0.7V_{CC}	-	V_{CC} + 0.3	V
		C2 version				
		V_{CC} = 5 V or 3V	0.6V_{CC}	-	V_{CC} + 0.3	V
		V_{CC} = 1.8 V	1.55	-	V_{CC} + 0.3	V
V_{hys}	hysteresis voltage	pin I/O	-	50	-	mV
I_{IL}	LOW-level input current	pin I/O; V_{IL} = 0 V	-	-	600	µA
I_{IH}	HIGH-level input current	pin I/O; V_{IH} = V_{CC}	-	-	10	µA
$t_{r(i)}$	input rise time	V_{IL} maximum to V_{IH} minimum	-	-	1.2	µs
$t_{r(o)}$	output rise time	$C_L \leq$ 80 pF; 10 % to 90 %; 0 V to V_{CC}	-	-	0.1	µs
$t_{f(i)}$	input fall time	V_{IL} maximum to V_{IH} minimum	-	-	1.2	µs
$t_{f(o)}$	output fall time	$C_L \leq$ 80 pF; 10 % to 90 %; 0 V to V_{CC}	-	-	0.1	µs
R_{pu}	pull-up resistance	connected to V_{CC}	7	9	11	kΩ

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Table 7. Characteristics of IC supply voltage *...continued*

V_{DDP} = 5 V; V_{DD} = 3.3 V; $V_{DD(INTF)}$ = 3.3 V; f_{xtal} = 10 MHz; GND = 0 V; T_{amb} = 25 °C; for C1 and C2 versions; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{pu}	pull-up current	$V_{OH} = 0.9V_{CC}$; C = 80 pF	−8	−6	−4	mA
Data lines to the system: pins I/OUC, AUX1UC and AUX2UC[4]						
V_{OL}	LOW-level output voltage	I_{OL} = 1 mA	0	-	0.3	V
V_{OH}	HIGH-level output voltage	no DC load	$0.9V_{DD(INTF)}$	-	$V_{DD(INTF)}$ + 0.1	V
		$I_{OH} \leq 40$ µA; $V_{DD(INTF)} > 2$ V	$0.75V_{DD(INTF)}$	-	$V_{DD(INTF)}$ + 0.1	V
		$I_{OH} \leq 20$ µA; $V_{DD(INTF)} < 2$ V	$0.75V_{DD(INTF)}$	-	$V_{DD(INTF)}$ + 0.1	V
V_{IL}	LOW-level input voltage		−0.3	-	$+0.3V_{DD(INTF)}$	V
V_{IH}	HIGH-level input voltage		$0.7V_{DD(INTF)}$	-	$V_{DD(INTF)}$ + 0.3	V
V_{hys}	hysteresis voltage	pin I/OUC	-	$0.14V_{DD(INTF)}$	-	V
I_{IH}	HIGH-level input current	$V_{IH} = V_{DD(INTF)}$	-	-	10	µA
I_{IL}	LOW-level input current	V_{IL} = 0 V	-	-	600	µA
R_{pu}	pull-up resistance	connected to $V_{DD(INTF)}$	8	10	12	kΩ
$t_{r(i)}$	input rise time	V_{IL} maximum to V_{IH} minimum	-	-	1.2	µs
$t_{r(o)}$	output rise time	$C_L \leq 30$ pF; 10 % to 90 %; 0 V to $V_{DD(INTF)}$	-	-	0.1	µs
$t_{f(i)}$	input fall time	V_{IL} maximum to V_{IH} minimum	-	-	1.2	µs
$t_{f(o)}$	output fall time	$C_L \leq 30$ pF; 10 % to 90 %; 0 V to $V_{DD(INTF)}$	-	-	0.1	µs
I_{pu}	pull-up current	$V_{OH} = 0.9V_{DD}$; C = 30 pF	−1	-	-	mA
Internal oscillator						
$f_{osc(int)}$	internal oscillator frequency	Shutdown mode	100	150	200	kHz
		active state	2	2.7	3.2	MHz
Reset output to the card: pin RST						
V_o	output voltage	Shutdown mode				
		no load	0	-	0.1	V
		I_o = 1 mA	0	-	0.3	V
I_o	output current	Shutdown mode; pin RST grounded	-	-	−1	mA
t_d	delay time	between pins RSTIN and RST; RST enabled	-	-	2	µs
V_{OL}	LOW-level output voltage	$I_{OL} = 200$ µA; V_{CC} = 5 V	0	-	0.3	V
		$I_{OL} = 200$ µA; V_{CC} = 3 V or 1.8 V	0	-	0.2	V
		current limit I_{OL} = 20 mA	$V_{CC} - 0.4$	-	V_{CC}	V
V_{OH}	HIGH-level output voltage	$I_{OH} = -200$ µA	$0.9V_{CC}$	-	V_{CC}	V
		current limit I_{OH} = −20 mA	0	-	0.4	V

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Table 7. Characteristics of IC supply voltage *...continued*

V_{DDP} = 5 V; V_{DD} = 3.3 V; $V_{DD(INTF)}$ = 3.3 V; f_{xtal} = 10 MHz; GND = 0 V; T_{amb} = 25 °C; for C1 and C2 versions; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_r	rise time	C_L = 100 pF	-	-	0.1	µs
t_f	fall time	C_L = 100 pF	-	-	0.1	µs
Clock output to the card: pin CLK						
V_o	output voltage	Shutdown mode				
		no load	0	-	0.1	V
		I_o = 1 mA	0	-	0.3	V
I_o	output current	Shutdown mode; pin CLK grounded	-	-	−1	mA
V_{OL}	LOW-level output voltage	I_{OL} = 200 µA - C1 version	0	-	0.3	V
		I_{OL} = 200 µA - C2 version	0	-	0.15 V_{CC}	V
		current limit I_{OL} = 70 mA	V_{CC} − 0.4	-	V_{CC}	V
V_{OH}	HIGH-level output voltage	I_{OH} = −200 µA	0.9V_{CC}	-	V_{CC}	V
		current limit I_{OH} = −70 mA	0	-	0.4	V
t_r	rise time	C_L = 30 pF [5]	-	-	16	ns
t_f	fall time	C_L = 30 pF [5]	-	-	16	ns
f_{CLK}	frequency on pin CLK	operational	0	-	20	MHz
δ	duty cycle	C_L = 30 pF [5]	45	-	55	%
SR	slew rate	rise and fall; C_L = 30 pF				
		V_{CC} = 5 V	0.2	-	-	V/ns
		V_{CC} = 3 V or 1.8 V	0.12	-	-	V/ns
Control inputs: pins CLKDIV1, CLKDIV2, RSTIN, VCC_SEL1 and VCC_SEL2[6]						
V_{IL}	LOW-level input voltage		−0.3	-	0.3$V_{DD(INTF)}$	V
V_{IH}	HIGH-level input voltage		0.7 $V_{DD(INTF)}$	-	$V_{DD(INTF)}$ + 0.3	V
V_{hys}	hysteresis voltage	control input	-	0.14$V_{DD(INTF)}$	-	V
I_{IL}	LOW-level input current	V_{IL} = 0 V	-	-	1	µA
I_{IH}	HIGH-level input current	V_{IH} = $V_{DD(INTF)}$	-	-	1	µA
Control input: pin CMDVCCN[6]						
V_{IL}	LOW-level input voltage		−0.3	-	0.3$V_{DD(INTF)}$	V
V_{IH}	HIGH-level input voltage		0.7$V_{DD(INTF)}$	-	$V_{DD(INTF)}$ + 0.3	V
V_{hys}	hysteresis voltage	control input	-	0.14$V_{DD(INTF)}$	-	V
I_{IL}	LOW-level input current	V_{IL} = 0 V	-	-	1	µA
I_{IH}	HIGH-level input current	V_{IH} = $V_{DD(INTF)}$	-	-	1	µA
$f_{CMDVCCN}$	frequency on pin CMDVCCN		-	-	100	Hz

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Table 7. Characteristics of IC supply voltage *...continued*

V_{DDP} = 5 V; V_{DD} = 3.3 V; $V_{DD(INTF)}$ = 3.3 V; f_{xtal} = 10 MHz; GND = 0 V; T_{amb} = 25 °C; for C1 and C2 versions; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_w	pulse width	5 V card	30	-	-	ms
		3 V card	-	-	15	ms
Card detection input: pin PRESN[6][7]						
V_{IL}	LOW-level input voltage		−0.3	-	$0.3V_{DD(INTF)}$	V
V_{IH}	HIGH-level input voltage		$0.7V_{DD(INTF)}$	-	$V_{DD(INTF)}$ + 0.3	V
V_{hys}	hysteresis voltage	pin PRESN	-	$0.14V_{DD(INTF)}$	-	V
I_{IL}	LOW-level input current	$0 V < V_{IL} < V_{DD(INTF)}$	-	-	5	µA
I_{IH}	HIGH-level input current	$0 V < V_{IH} < V_{DD(INTF)}$	-	-	5	µA
OFFN output[8]						
V_{OL}	LOW-level output voltage	I_{OL} = 2 mA	0	-	0.3	V
V_{OH}	HIGH-level output voltage	I_{OH} = −15 µA	$0.75V_{DD(INTF)}$	-	-	V
R_{pu}	pull-up resistance	connected to $V_{DD(INTF)}$	16	20	24	kΩ

[1] To meet these specifications, V_{CC} should be decoupled to pin GND using two ceramic multilayer capacitors of low ESR with values of one 220 nF and one 470 nF.

[2] Using decoupling capacitors of one 220 nF ±20 % and one 470 nF ±20 %.

[3] Using the integrated 9 kΩ pull-up resistor connected to V_{CC}.

[4] Using the integrated 10 kΩ pull-up resistor connected to $V_{DD(INTF)}$.

[5] The transition time and the duty factor definitions are shown in Figure 11 on page 21; δ = t1 / (t1 + t2).

[6] Pins PRESN and CMDVCCN are active LOW; pin RSTIN is active HIGH; see Table 4 for states of pins CLKDIV1 and CLKDIV2.

[7] Pin PRESN has an integrated current source of 1.25 µA to $V_{DD(INTF)}$.

[8] Pin OFFN is an NMOS drain, using an internal 20 kΩ pull-up resistor connected to $V_{DD(INTF)}$.

Table 8. Protection characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{Olim}	output current limit	pin I/O	−15	-	+15	mA
		pin V_{CC}	135	175	225	mA
		pin CLK	−70	-	+70	mA
		pin RST	−20	-	+20	mA
I_{sd}	shutdown current	pin V_{CC}	90	120	150	mA
T_{sd}	shutdown temperature	at die	-	150	-	°C

Table 9. Timing characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{act}	activation time	see Figure 7 on page 11	2090	-	4160	µs
t_{deact}	deactivation time	see Figure 8 on page 12	35	90	250	µs

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Table 9. Timing characteristics *…continued*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_d	delay time	CLK sent to card using an external clock				
		$t_{d(start)}$ = t3; see Figure 7 on page 11	2090	-	4112	µs
		$t_{d(end)}$ = t5; see Figure 7 on page 11	2120	-	4160	µs
t_{deb}	debounce time	pin PRESN	3.2	4.5	6.4	ms

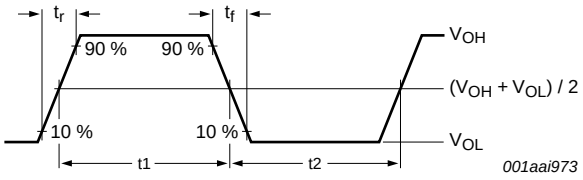


Fig 11. Definition of output and input transition times

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12. Application information

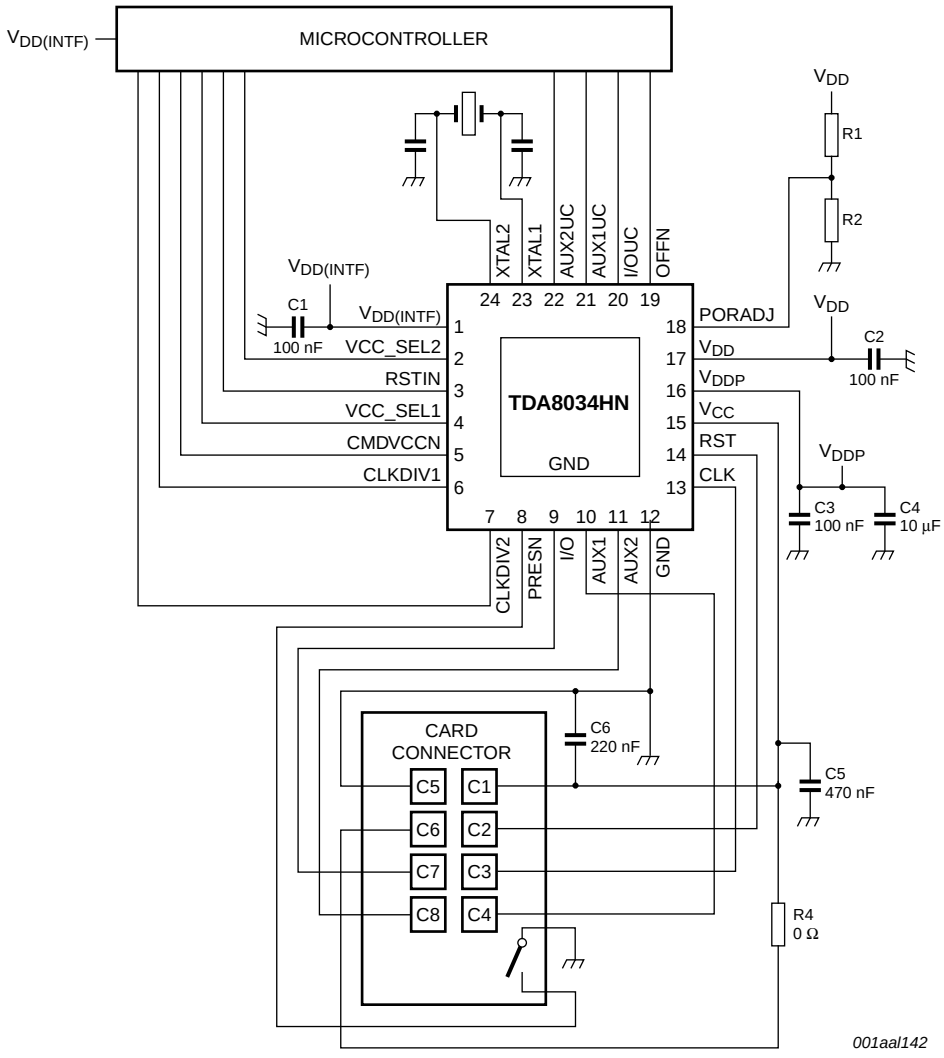


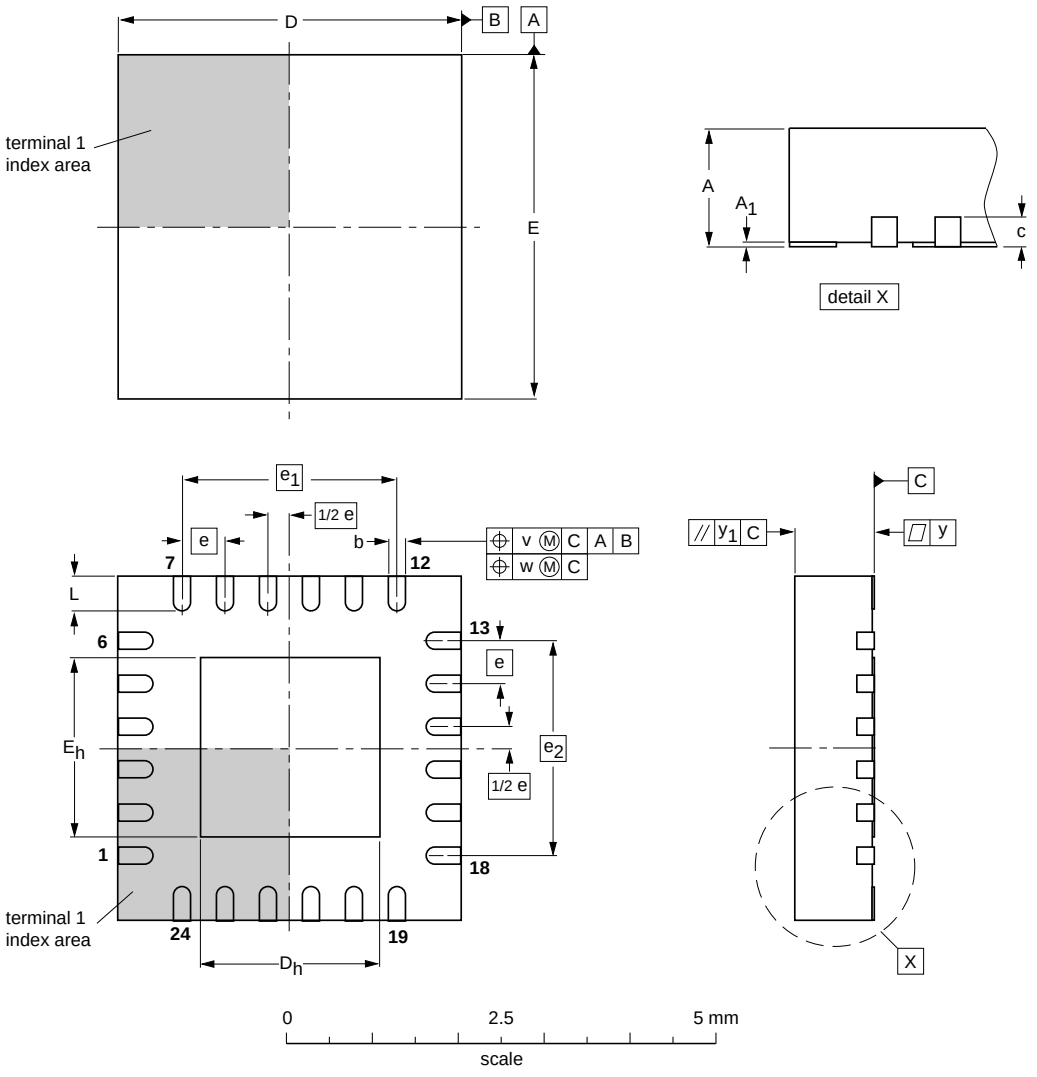
Fig 12. Application diagram

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13. Package outline

HVQFN24: plastic thermal enhanced very thin quad flat package; no leads; 24 terminals; body 4 x 4 x 0.85 mm **SOT616-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max.	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	e_2	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	4.1 3.9	2.25 1.95	4.1 3.9	2.25 1.95	0.5	2.5	2.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT616-1	- - -	MO-220	- - -			~~01-08-08~~ 02-10-22

Fig 13. Package outline SOT616-1 (HVQFN24)

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14. Soldering of SMD packages

This text provides a very brief insight into a complex technology. A more in-depth account of soldering ICs can be found in Application Note *AN10365 "Surface mount reflow soldering description"*.

14.1 Introduction to soldering

Soldering is one of the most common methods through which packages are attached to Printed Circuit Boards (PCBs), to form electrical circuits. The soldered joint provides both the mechanical and the electrical connection. There is no single soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and Surface Mount Devices (SMDs) are mixed on one printed wiring board; however, it is not suitable for fine pitch SMDs. Reflow soldering is ideal for the small pitches and high densities that come with increased miniaturization.

14.2 Wave and reflow soldering

Wave soldering is a joining technology in which the joints are made by solder coming from a standing wave of liquid solder. The wave soldering process is suitable for the following:

- Through-hole components
- Leaded or leadless SMDs, which are glued to the surface of the printed circuit board

Not all SMDs can be wave soldered. Packages with solder balls, and some leadless packages which have solder lands underneath the body, cannot be wave soldered. Also, leaded SMDs with leads having a pitch smaller than ~0.6 mm cannot be wave soldered, due to an increased probability of bridging.

The reflow soldering process involves applying solder paste to a board, followed by component placement and exposure to a temperature profile. Leaded packages, packages with solder balls, and leadless packages are all reflow solderable.

Key characteristics in both wave and reflow soldering are:

- Board specifications, including the board finish, solder masks and vias
- Package footprints, including solder thieves and orientation
- The moisture sensitivity level of the packages
- Package placement
- Inspection and repair
- Lead-free soldering versus SnPb soldering

14.3 Wave soldering

Key characteristics in wave soldering are:

- Process issues, such as application of adhesive and flux, clinching of leads, board transport, the solder wave parameters, and the time during which components are exposed to the wave
- Solder bath specifications, including temperature and impurities

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14.4 Reflow soldering

Key characteristics in reflow soldering are:

- Lead-free versus SnPb soldering; note that a lead-free reflow process usually leads to higher minimum peak temperatures (see Figure 14) than a SnPb process, thus reducing the process window
- Solder paste printing issues including smearing, release, and adjusting the process window for a mix of large and small components on one board
- Reflow temperature profile; this profile includes preheat, reflow (in which the board is heated to the peak temperature) and cooling down. It is imperative that the peak temperature is high enough for the solder to make reliable solder joints (a solder paste characteristic). In addition, the peak temperature must be low enough that the packages and/or boards are not damaged. The peak temperature of the package depends on package thickness and volume and is classified in accordance with Table 10 and 11

Table 10. SnPb eutectic process (from J-STD-020D)

Package thickness (mm)	Package reflow temperature (°C)	
	Volume (mm^3)	
	< 350	≥ 350
< 2.5	235	220
≥ 2.5	220	220

Table 11. Lead-free process (from J-STD-020D)

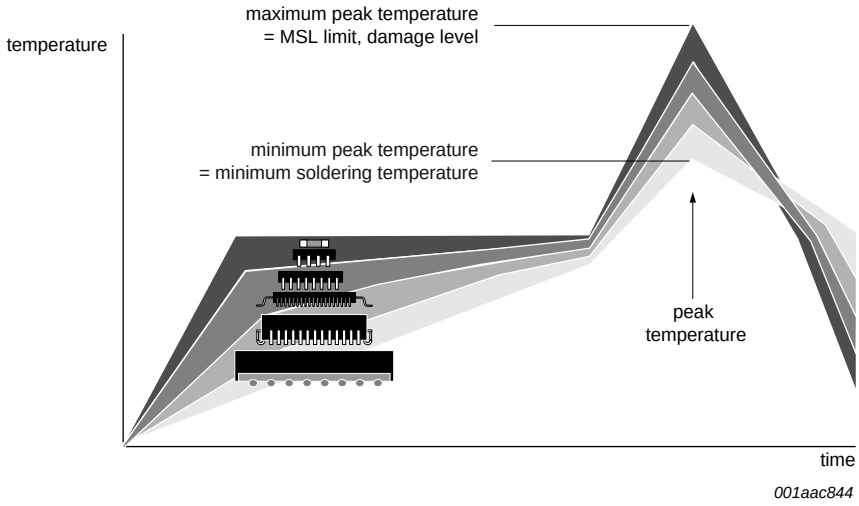
Package thickness (mm)	Package reflow temperature (°C)		
	Volume (mm^3)		
	< 350	350 to 2000	> 2000
< 1.6	260	260	260
1.6 to 2.5	260	250	245
> 2.5	250	245	245

Moisture sensitivity precautions, as indicated on the packing, must be respected at all times.

Studies have shown that small packages reach higher temperatures during reflow soldering, see Figure 14.

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MSL: Moisture Sensitivity Level

Fig 14. Temperature profiles for large and small components

For further information on temperature profiles, refer to Application Note *AN10365 "Surface mount reflow soldering description"*.

15. Abbreviations

Table 12. Abbreviations

Acronym	Description
EMV	Europay MasterCard VISA
ESD	ElectroStatic Discharge
ESR	Equivalent Series Resistor
FCDM	Field Charged Device Model
HBM	Human Body Model
LDO	Low Drop-Out
MM	Machine Model
NMOS	Negative-channel Metal-Oxide Semiconductor
POR	Power-On Reset

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16. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice-	Supersedes
TDA8034HN v.3.5	20200313	Product data sheet	-	TDA8034HN v.3.4
Modifications:	• Section 8.1 “Power supplies”: Last paragraph added			
TDA8034HN v.3.4	20160629	Product data sheet	-	TDA8034HN v3.3
Modifications:	• Section 5 “Ordering information”: C2 version added (EMVCo 4.3 compliant) • Table 7 “Characteristics of IC supply voltage”: values for C2 version added			
TDA8034HN v.3.3	20150520	Product data sheet	-	TDA8034HN v3.2
Modifications:	• Section 2 “Features and benefits”: ESD value updated • Table 5 “Limiting values”: V_{ESD} values updated			
TDA8034HN v.3.2	20140325	Product data sheet	-	TDA8034HN v.3.1
Modifications:	• Change of descriptive title • Section 2 “Features and benefits”: typos corrected			
TDA8034HN v.3.1	20110905	Product data sheet	-	TDA8034HN v.3.0
Modifications:	• Table 1 “Quick reference data”: values added • Table 7 “Characteristics of IC supply voltage”: values added • Figure 1 “Block diagram”: Figure note (1) changed			
TDA8034HN v.3.0	20110117	Product data sheet	-	TDA8034HN v.2.0
Modifications:	• Table 2 “Ordering information”: type number updated into TDA8034HN/C1 • Table 3 “Pin description”: Table note [2] corrected			
TDA8034HN v.2.0	20101112	Product data sheet	-	TDA8034HN_1
Modifications:	• Table 3 “Pin description”: Table note [4] V_{DD} changed into $V_{DD(INTF)}$ Table note [5] added IOUC, AUX1UC, AUX2UC referenced to new note [5]			
TDA8034HN_1	20100205	Product data sheet	-	-

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19. Tables

Table 1. Quick reference data 2
Table 2. Ordering information 3
Table 3. Pin description 5
Table 4. Clock configuration 8
Table 5. Limiting values 14
Table 6. Thermal characteristics 15
Table 7. Characteristics of IC supply voltage 15
Table 8. Protection characteristics 20
Table 9. Timing characteristics 20
Table 10. SnPb eutectic process (from J-STD-020D) . . .25
Table 11. Lead-free process (from J-STD-020D) 25
Table 12. Abbreviations 26
Table 13. Revision history 27

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20. Figures

Fig 1. Block diagram 4
Fig 2. Pin configuration 5
Fig 3. Voltage supervisor circuit 7
Fig 4. Voltage supervisor waveforms 7
Fig 5. Basic layout for using an external clock 8
Fig 6. Shutdown and Deep shutdown mode activation/deactivation 10
Fig 7. Activation sequence at t3 11
Fig 8. Deactivation sequence 12
Fig 9. Emergency deactivation sequence after card removal 13
Fig 10. Operation of debounce feature with pins OFFN, CMDVCCN, PRESN and V_{CC} 14
Fig 11. Definition of output and input transition times . . .21
Fig 12. Application diagram 22
Fig 13. Package outline SOT616-1 (HVQFN24) 23
Fig 14. Temperature profiles for large and small components 26

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21. Contents

1 General description 1
2 Features and benefits 1
3 Applications 2
4 Quick reference data 2
5 Ordering information 3
6 Block diagram 4
7 Pinning information 5
7.1 Pinning 5
7.2 Pin description 5
8 Functional description 6
8.1 Power supplies 6
8.2 Voltage supervisor 7
8.3 Clock circuits 8
8.4 Input and output circuits 9
8.5 Shutdown mode 9
8.6 Deep shutdown mode 9
8.7 Activation sequence 10
8.8 Deactivation sequence 11
8.9 V_{CC} regulator 12
8.10 Fault detection 12
9 Limiting values 14
10 Thermal characteristics 15
11 Characteristics 15
12 Application information 22
13 Package outline 23
14 Soldering of SMD packages 24
14.1 Introduction to soldering 24
14.2 Wave and reflow soldering 24
14.3 Wave soldering 24
14.4 Reflow soldering 25
15 Abbreviations 26
16 Revision history 27
17 Legal information 28
17.1 Data sheet status 28
17.2 Definitions 28
17.3 Disclaimers 28
17.4 Trademarks 29
18 Contact information 29
19 Tables 30
20 Figures 31
21 Contents 32

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